Ferromagnetism near three-quarters filling in twisted bilayer graphene

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arXiv: 1901.03520



Cao, *Nature* (2018)



Jarillo-Herrero and Kaxiras groups

### Impact of Alignment with hBN

Device 1: aligned hBN



Graphene twist: 1.20 +/- 0.01° Twist to one hBN: 0.81° +/- 0.02°



Device 2: misaligned hBN



Graphene twist: 1.05 +/- 0.01° Twist to hBN: large



### Impact of Alignment with hBN



Device 2: misaligned hBN



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## Alignment with hBN

Opens a gap at charge neutrality



Amet, *PRL* (2013) Hunt, *Science* (2013)

Monolayer graphene



Monolayer graphene + hBN



### Measuring Hall Slope Density Dependence



### Emergent Ferromagnetism at <sup>3</sup>/<sub>4</sub> Filling



### Anomalous Hall Signal Can Be Really Large!



### Comparison: Quantum Anomalous Hall in (Cr,Bi,Sb)<sub>2</sub>Te<sub>3</sub>



Material & device:

6 QL Cr<sub>0.24</sub>(Bi<sub>0.3</sub>Sb<sub>0.7</sub>)<sub>1.76</sub>Te<sub>3</sub> GaAs substrate Ti/Au contacts Top gate

# $\begin{aligned} & \mathsf{ldeally} \\ & \rho_{xx} = 0 \\ & \rho_{yx} = h/e^2 \approx 26 \mathrm{k}\Omega \end{aligned}$



### Near optimal gate voltage



### Comparison: Anomalous Hall in TBG

Far from quantization



### Nature of Emergent Ferromagnetism at <sup>3</sup>/<sub>4</sub> Filling?

Simplistic band diagram: what *might* be happening...



Twisted bilayer graphene + hBN



Zhang, *arXiv:1901.08209* Bultinck, *arXiv:1901.08110* 

Gap may open spontaneously Xie, *arXiv:1812.04213* 

### Repeatable Hysteresis in Current

Another TBG Mystery











TBG becomes ferromagnetic near <sup>3</sup>/<sub>4</sub> filling up to 5 K!

Alignment to hBN may be crucial

At optimal doping  $\rho_{xy} = 10.4 \text{ k}\Omega$  $\rho_{xy} / \rho_{xx} = 1.4$ 

Evidence for edge conduction

Small DC current can flip magnetization

arXiv: 1901.03520



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